

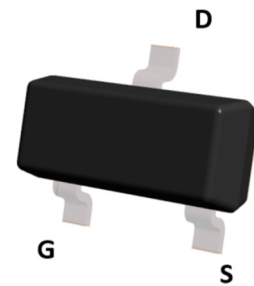
Description

- Trench Power LV MOSFET technology
- High Power and Current handling capability
- Low Gate Charge

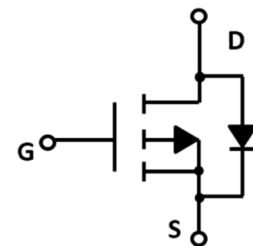
MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
-20	90@ $V_{GS} = -4.5V$	-4.0
	135@ $V_{GS} = -2.5V$	

Applications

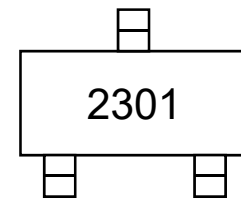
- PWM applications
- Load switch
- Power management



Top View



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_A=25^\circ C$ @ Steady State	I_D	-4.0	A
	$T_A=70^\circ C$ @ Steady State		-3.0	
Pulsed Drain Current ¹⁾		I_{DM}	-14	A
Total Power Dissipation @ $T_A=25^\circ C$		P_D	1	W
Thermal Resistance Junction-to-Ambient @ Steady State ²⁾		$R_{\theta JA}$	125	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

Notes:

1) Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2) Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.5	-0.75	-1.1	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -3.0A	-	-	90	mΩ
		V _{GS} = -2.5V, I _D = -2.0A	-	-	135	
Diode Forward Voltage	V _{SD}	I _S = -4.0A, V _{GS} = 0V	-	-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	-4.0	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	-	550	-	pF
Output Capacitance	C _{oss}		-	89	-	
Reverse Transfer Capacitance	C _{rss}		-	65	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4.0A	-	4.3	-	nC
Gate Source Charge	Q _{gs}		-	0.8	-	
Gate Drain Charge	Q _{gd}		-	1.1	-	
Turn-on Delay Time	t _{D(on)}	V _{GS} = -4.5V, V _{DD} = -10V, I _D = -1A, R _{GEN} = 2.5Ω	-	12	-	ns
Turn-on Rise Time	t _r		-	54	-	
Turn-off Delay Time	t _{D(off)}		-	15	-	
Turn-off Fall Time	t _f		-	9	-	

Typical Characteristics

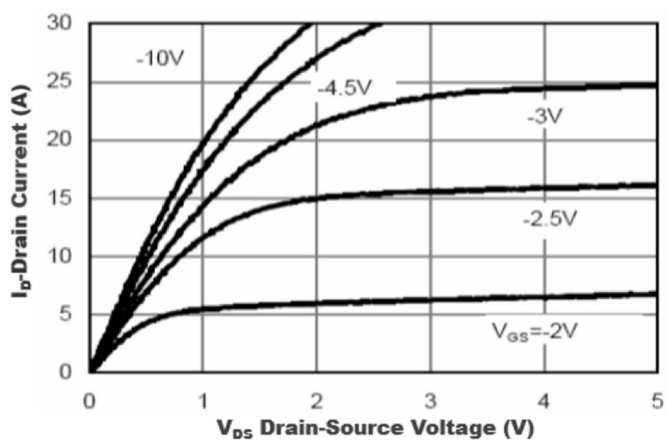


Figure1. Output Characteristics

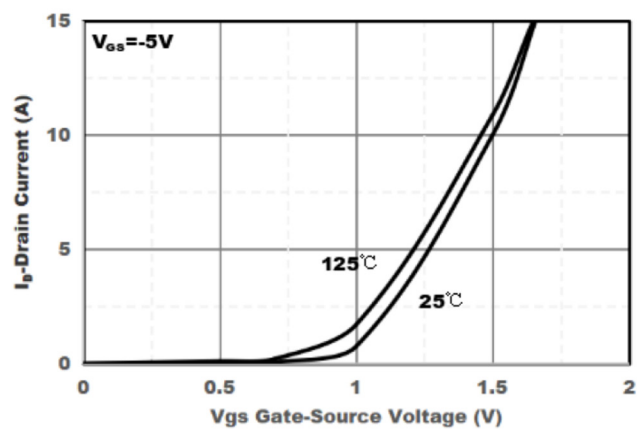


Figure2. Transfer Characteristics

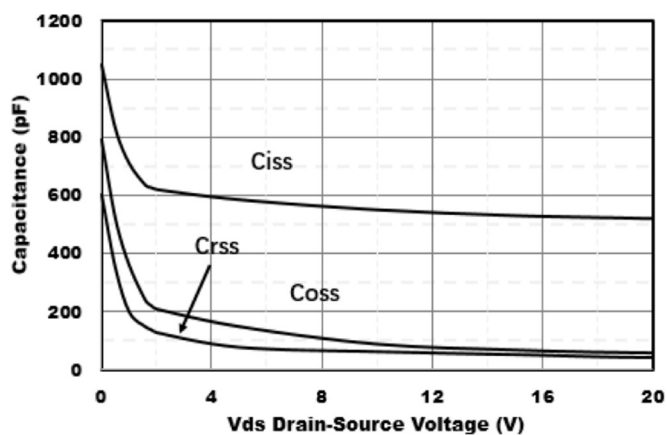


Figure3. Capacitance Characteristics

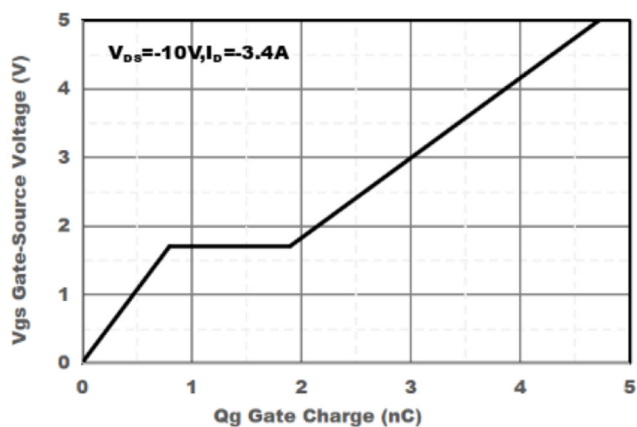


Figure4. Gate Charge

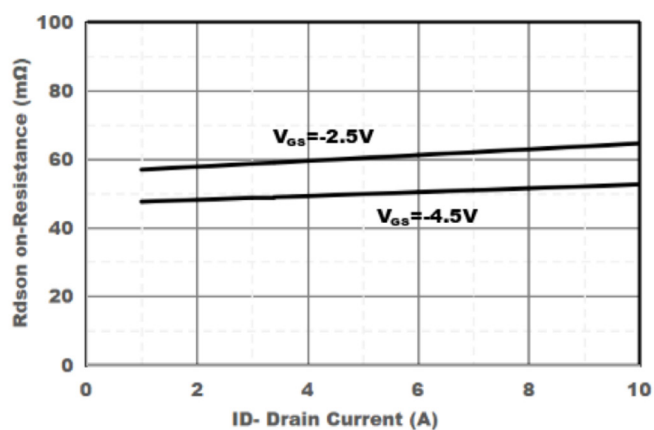


Figure5. Drain-Source on Resistance

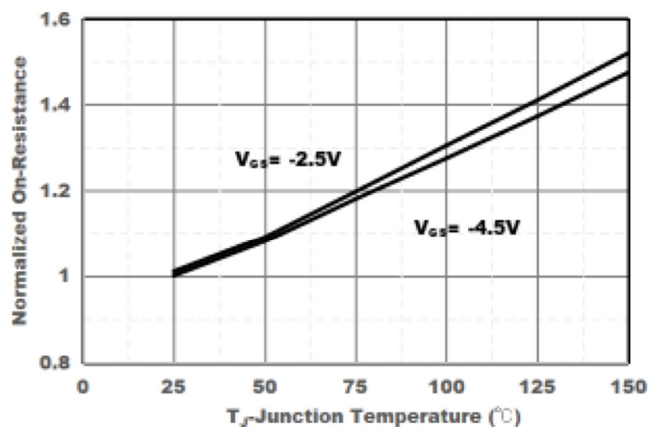
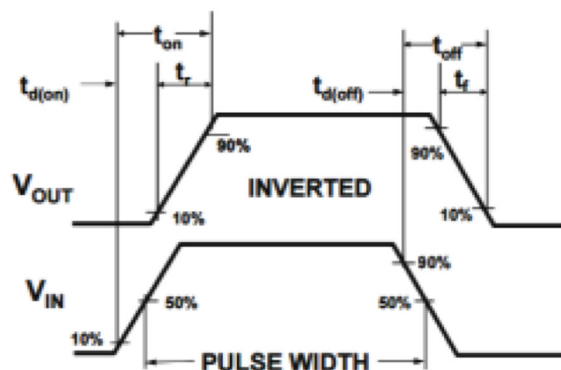
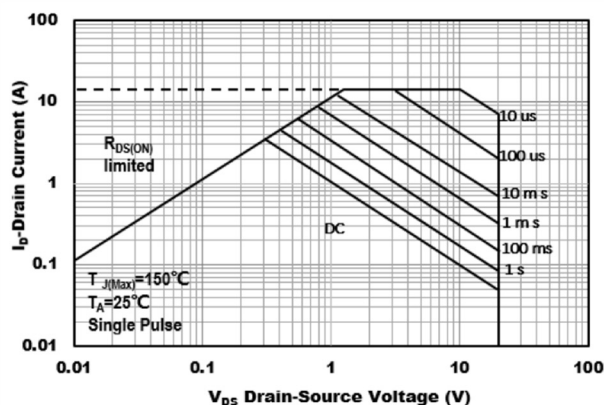



Figure6. Drain-Source on Resistance




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